Abstract

Method for the Local Polishing of a Semiconductor Wafer

A method for locally polishing one side of a semiconductor wafer, in which the semiconductor wafer is pressed by means of a rotatable polishing head with its side surface to be polished against a polishing pad lying on a rotating polishing plate and containing fixed abrasive, wherein the polishing head is provided with a resilient membrane and radially subdivided into a plurality of chambers by means of gas or liquid cushions, and the exerted polishing pressure can be selected differently for each chamber, wherein the semiconductor wafer is held in position during this by a retainer ring which is likewise pressed against the polishing pad with an application pressure, wherein a polishing agent is introduced between the semiconductor wafer and the polishing pad, and the polishing pressure exerted on the semiconductor wafer in a chamber lying in the edge region of the semiconductor wafer of the polishing head, and the application pressure of the retainer ring, are selected so that material is essentially removed only at the edge of the semiconductor wafer.

No Figure.